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TOSHIBA CORPORATION

Semiconductor Company

Document Change Notification

The purpose of this notification is to inform customers about the launch of the Pb-free version of the device. The introduction of a Pb-free replacement affects the datasheet. Please understand that this notification is intended as a temporary substitute for a revision of the datasheet.

Changes to the datasheet may include the following, though not all of them may apply to this particular device.

- 1. Part number
 - Example: TMPxxxxxF TMPxxxxxFG

All references to the previous part number were left unchanged in body text. The new part number is indicated on the prelims pages (cover page and this notification).

2. Package code and package dimensions

Example: LQFP100-P-1414-0.50C LQFP100-P-1414-0.50F

All references to the previous package code and package dimensions were left unchanged in body text. The new ones are indicated on the prelims pages.

3. Addition of notes on lead solderability

Now that the device is Pb-free, notes on lead solderability have been added.

4. RESTRICTIONS ON PRODUCT USE

The previous (obsolete) provision might be left unchanged on page 1 of body text. A new replacement is included on the next page,

5. Publication date of the datasheet

The publication date at the lower right corner of the prelims pages applies to the new device.

1. Part number

2. Package code and dimensions

F	Previous Part Number (in Body Text)	Previous Package Code (in Body Text)	New Part Number	New Package Code	OTP
	TMP87PM14N	SDIP64-P-750-1.78	TMP87PM14NG	SDIP64-P-750-1.78	—
	TMP87PM14F	QFP64-P-1420-1.00A	TMP87PM14FG	QFP64-P-1420-1.00A	—

*: For the dimensions of the new package, see the attached Package Dimensions diagram.

3. Addition of notes on lead solderability

The following solderability test is conducted on the new device.

Lead solderability of Pb-free devices (with the G suffix)

Test	Test Conditions	Remark
Solderability	 (1) Use of Lead (Pb) solder bath temperature = 230°C dipping time = 5 seconds the number of times = once use of R-type flux (2) Use of Lead (Pb)-Free solder bath temperature = 245°C dipping time = 5 seconds the number of times = once use of R-type flux 	Leads with over 95% solder coverage till lead forming are acceptable.

4. RESTRICTIONS ON PRODUCT USE

The following replaces the "RESTRICTIONS ON PRODUCT USE" on page 1 of body text.

RESTRICTIONS ON PRODUCT USE

• The information contained herein is subject to change without notice.

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- For a discussion of how the reliability of microcontrollers can be predicted, please refer to Section 1.3 of the chapter entitled Quality and Reliability Assurance/Handling Precautions.

5. Publication date of the datasheet

The publication date of this datasheet is printed at the lower right corner of this notification.

(Annex)

Package Dimensions

SDIP64-P-750-1.78



QFP64-P-1420-1.00A

Unit: mm



CMOS 8-Bit Microcontroller

TMP87PM14N/F

The 87PM14 is a One-Time PROM microcontroller with low-power 256 K bits (32 Kbytes) electrically programmable read only memory for the 87C814/CH14/CK14/CM14 system evaluation. The 87PM14 is pin compatible with the 87C814/CH14/CK14/CM14. The operations possible with the 87C814/CH14/CK14/CM14 can be performed by writing programs to PROM. The 87PM14 can write and verify in the same way as the TC27256 using an adaptor socket BM1198/BM1199 and an EPROM programmer.

Part No.	OTP	RAM	Package	Adaptor socket
TMP87PM14N			P-SDIP64-750-1.78	BM1198
TMP87PM14F	32K x 8-bit	1K x 8- bit	P-QFP64-1420-1.00A	BM1199



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- For a discussion of how the reliability of microcontrollers can be predicted, please refer to Section 1.3 of the chapter entitled Quality and Reliability Assurance / Handling Precautions.
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Pin Assignments (Top View)



Pin Function

The 87PM14 has two modes two modes: MCU and PROM.

(1) MCU mode

In this mode, the 87PM14 is pin compatible with the 87C814/CH14/CK14/CM14 (fix the TEST pin at low level).

(2) PROM mode

Pin Name (PROM mode)	Input / Output	Functions	Pin Name (MCU mode)	
A14 A13 to A10 A9 A8	Input	PROM address inputs	VAREF P33 to P30 P15 P12	
A7 to A0			P67 to P60	
D7 to D0	I/O	PROM data input/outputs	P07 to P00	
CE	lasaut	Chip enable signal input (active low)	P13	
ŌĒ	Input	Input Output enable signal input (active low)		
VPP		+ 12.5 V / 5 V (Program supply voltage)	TEST	
vcc	Power supply	+5V	VDD	
GND	(VSS	
P11 P21 P87		PROM mode setting pin. Be fixed at high level.		
P10, P16, P17 P22, P20 RESET		PROM mode setting pin. Be fixed at low level.		
XIN XOUT	Input output	Connect an 8 MHz oscillator to stabilize the internal s	tate.	
P57 to P50 P77 to P70	> 1/0	Open		
P86 to P80 VASS	Power supply	Open		
VA35	VFT Power supply	Open 0 V (GND)		
VON	v r r Power supply			

OPERATIONAL DESCRIPTION

The following explains the 87PM14 hardware configuration and operation. The configuration and functions of the 87PM14 are the same as those of the 87C814/CH14/CK14/CM14, except in that a one-time PROM is used instead of an on-chip mask ROM.

The 87PM14 is placed in the *single-clock* mode during reset. To use the dual-clock mode, the low-frequency oscillator should be turned on by executing [SET (SYSCR2). XTEN] instruction at the beginning of the program.

1. OPERATING MODE

The 87PM14 has two modes: MCU and PROM.

1.1 MCU Mode

The MCU mode is activated by fixing the TEST / VPP pin at low level. In the MCU mode, operation is the same as with the 87C814/CH14/CK14/CM14 (the TEST / VPP pin cannot be used open because it has no built-in pull-down resistance).

1.1.1 Program Memory

The 87PM14 has a $32K \times 8$ -bit (addresses 8000_{H} -FFFF_H in the MCU mode, addresses 0000_{H} -7FFF_H in the PROM mode) of program memory (OTP). To use the 87PM14 as the system evaluation for the 87C814/CH14/CK14/CM14 the program should be written to the program memory area as shown in Figure 1-1.



Either write the data FF_H to the unused area or set the PROM programmer to access only the program storage area.

1.1.2 Data Memory

The 87PM14 has an on-chip $1k \times 8$ -bit data memory (static RAM).

1.1.3 Input/Output Circuitry

(1) Control pins

The control pins of the 87PM14 are the same as those of the 87C814/CH14/CK14/CM14 except that the TEST pin has is no built-in pull-down resistance.



(2) I/O ports

The I/O circuitries of 87PM14 I/O ports are the same as the code A type I/O circuitries of the 87C814/CH14/CK14/CM14.

1.2 PROM Mode

The PROM mode is activated by setting the pins TEST, RESET and the ports P17-P10, P22-P20 and P87 as shown in Figure 1-3. The PROM mode is used to write and verify programs with a general-purpose PROM programmer. The high-speed programming mode can be used for program operation.

The 87PM14 is not supported an electric signature mode, so the ROM type must be set to TC27256.

Set the adaptor socket switch to "N".

Note: Please set the high-speed programming mode according to each manual of PROM program.





1.2.1 Programming Flowchart (High-speed Programming Mode-I)

The high-speed programming mode is achieved by applying the program voltage (+ 12.5 V) to the Vpp pin when Vcc = 6 V. After the address and input data are stable, the data is programmed by applying a single 1ms program pulse to the \overline{CE} input. The programmed data is verified. If incorrect, another 1ms program pulse is applied and then the programmed data is verified. This process should be repeated (up to 25 times) until the program operates correctly. Programming for one address is ended by applying additional program pulse with width 3 times that needed for initial programming (number of programmed times \times 1 ms). After that, change the address and input data, and program as before. When programming has been completed, the data in all addresses should be verified with Vcc = Vpp = 5 V.



Figure 1-4. Flowchart of High-speed Programming Mode - I

1.2.2 Programming Flowchart (High-speed Programming Mode-II)

The high-speed programming mode is achieved by applying the program voltage (+ 12.75 V) to the Vpp pin when Vcc = 6.25 V. After the address and input data are stable, the data is programmed by applying a single 0.1ms program pulse to the \overline{CE} input. The programmed data is verified. If incorrect, another 0.1ms program pulse is applied and then the programmed data is verified. This process should be repeated (up to 25 times) until the program operates correctly. After that, change the address and input data, and program as before. When programming has been completed, the data in all addresses should be verified with Vcc = Vpp = 5 V.



Figure 1-5. Flowchart of High-speed Programming Mode - ${\rm II}$

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(1) Adapters

1.2.3

BM1198: TMP87PM14N BM1199: TMP87PM14F (2) Adapter setting Switch (SW1) is set to side N. (3) PROM programmer specifying PROM type is specified to TC27256. i) Writing voltage: 12.5 V (high-speed program I mode) 12.75 V (high-speed program I mode) ii) Data transfer (copy) (note 1) In TMP87PM14, EPROM is within the addresses 0000 to 7FFFH. Data is required to be transferred (copied) to the addresses where it is possible to write. The program area in MCU mode and PROM mode is referred to "Program memory area" in Figure 1-1. Ex. In the block transfer (copy) mode, executed as below. ROM capacity of 32KB: transferred addresses 8000 to FFFFH to addresses 0000 to 7FFFH iii) Writing address is specified. (note 1) Start address: 0000H End address: 7FFFH (4) Writing Writing/Verifying is required to be executed in accordance with PROM programmer operating procedure. Note 1: The specifying method is referred to the PROM programmer description. The data in unused area must be specified to FF_H.

Writing Method for General-purpose PROM Program

- Note 2: When MCU is set to an adapter or the adapter is set to PROM programmer, a position of pin 1 must be adjusted. If the setting is reversed, MCU, the adapter and PROM program is damaged.
- Note 3: TMP87PM14 does not support the electric signature mode (hereinafter referred to as "signature"). If the signature is used in PROM program, a device is damaged due to applying 12V ± 0.5V to the address pin 9 (A9). The signature must not be used.

Electrical Characteristics

Absolute Maximum Rat	ings	(V _{SS} = 0 V)		
Parameter	Symbol	Pins	Ratings	Unit
Supply Voltage	V _{DD}		-0.3 to 6.5	V
Program Voltage	V _{PP}	TEST / VPP	– 0.3 to 13.0	V
Input Voltage	V _{IN}		– 0.3 to V _{DD} + 0.3	V
Output Voltage	V _{OUT1}	P0, P1, P2, P3, P6, XOUT, RESET	– 0.3 to V _{DD} + 0.3	v
	V _{OUT2}	Source open drain ports	$V_{DD} - 40$ to $V_{DD} + 0.3$	
	I _{OUT1}	P0, P1, P2, P3, P6	3.2	
Output Current (Per 1 pin)	I _{OUT2}	P8	12	mA
	I _{OUT3}	P5, P7	- 25	
	Σ I _{OUT1}	P0, P1, P2, P3, P6	120	
Output Current (Total)	ΣI_{OUT2}	P5, P7, P8	-120	mA
Power Dissipation [Topr = 25°C]	PD		600	mW
Soldering Temperature (time)	Tsld	$\langle \langle \rangle \rangle \langle \langle \rangle$	260 (10 s)	°C
Storage Temperature	Tstg		– 55 to 125	°C
Operating Temperature	Topr	2(> (/ 5)	– 30 to 70	°C

Note: The absolute maximum ratings are rated values which must not be exceeded during operation, even for an instant. Any one of the ratings must not be exceeded. If any absolute maximum rating is exceeded, a device may break down or its performance may be degraded, causing it to catch fire or explode resulting in jnjury to the user. Thus, when designing products which include this device, ensure that no absolute maximum rating value will ever be exceeded.

Recommended Operating Conditions $(V_{SS} = 0 \text{ V}, \text{ Topr} = -30 \text{ to } 70^{\circ}\text{C})$

			\sim	\sim			
Parameter	Symbol	Pins		Conditions	Min	Max	Unit
				NORMAL 1, 2 modes	4.5		
			fc = 8 MHz	IDLE1, 2 modes	4.5		
Supply Voltage	V _{DD}		fs =	SLOW mode	2.7	5.5	v
~	~		32.768 kHz	SLEEP mode	2.7		
\square	\mathbb{Z}_{\sim}		$\langle \rangle$	STOP mode	2.0		
Output Voltage	V _{OUT2}	Source open drain ports			V _{DD} – 38	V_{DD}	V
	V _{IH1}	Except hysteresis input	V >4 5 V		V _{DD} x 0.70		
Input High Voltage	tage V _{IH2} Hysteresis input	V _{DD} ≧4.5 V		V _{DD} x 0.75	V _{DD}	v	
	V _{IH3}	$\left(\left(\left(\right) \right) \right)$	V _{DD} <4.5 V		V _{DD} x 0.90		
	V _{IL1}	Except hysteresis input		V _{DD} ×		$V_{DD} \times 0.30$	
Input Low Voltage	V _{IL2}	Hysteresis input		V _{DD} ≧4.5 V	0	$V_{DD} \times 0.25$	V
\sim	V _{IL3}	~	V	′ _{DD} <4.5 V		V _{DD} x 0.10	
	fc	XIN, XOUT	V _{DD} =	= 4.5 V to 5.5 V	0.4	8.0	MHz
Clock Frequency	fs	XTIN, XTOUT			30.0	34.0	kHz

Note 1: The recommended operating conditions for a device are operating conditions under which it can be guaranteed that the device will operate as specified. If the device is used under operating conditions other than the recommended operating conditions (supply voltage, operating temperature range, specified AC/DC values etc.), malfunction may occur. Thus, when designing products which include this device, ensure that the recommended operating conditions for the device are always adhered to.

Note 2: Clock frequency fc: Supply voltage range is specified in NORMAL 1/2 mode and IDLE 1/2 mode.

D.C. Cha	racteris	ti cs (V _{SS} = 0 V, Top	or = – 30 to 70°C)				
Parameter	Symbol	Pins	Conditions	Min	Тур.	Max	Unit
Hysteresis Voltage	V _{HS}	Hysteresis input		$\langle - \rangle$	0.9	_	V
	I _{IN1}	TEST	V _{DD} = 5.5 V				
Input Current	I _{IN2}	Open drain ports, Tri-state ports	V _{IN} = 5.5 V/0 V	5)-	-	± 2	μA
	I _{IN3}	RESET, STOP		\mathcal{O}			
Input Resistance	R _{IN1}	RESET		100	220	450	
Dull dours Desistores	R ₁		$V_{DD} = 5.5 V, V_{OUT} = 5.5 V$	-	200	-	kΩ
Pull-down Resistance	R _K	Source open drain ports	$V_{DD} = 5.5 V, V_{KK} = -30 V$	-	80	-	
Output Leakage	I _{LO1}	Sink open drain ports	$V_{DD} = 5.5 V, V_{OUT} = 5.5 V$	- 0	1(-/	2	
Current	I _{LO2}	Source open drain ports	$V_{DD} = 5.5 V, V_{OUT} = -32 V$	-12	J	- 2	μA
Current	I _{LO3}	Tri-state ports	$V_{DD} = 5.5 V, V_{OUT} = 5.5 V / 0 V$	(f)	2	± 2	
Output High Voltage	V _{OH1}	Tri-state ports	$V_{DD} = 4.5 V, I_{OH} = -0.7 \text{ mA}$	4.1	$\mathcal{I}(\mathcal{A})$	-	v
Output high voltage	V _{OH2}	P8	$V_{DD} = 4.5 V, I_{OH} = -8 mA$	2.4	10/	-	v
Output Low Voltage	V _{OL}	Except XOUT	$V_{DD} = 4.5 V, I_{OL} = 1.6 mA$	\sim	<u> </u>	0.4	V
Output High current	I _{ОН}	P5, P7 🔿	$V_{DD} = 4.5 V, V_{OH} = 2.4 V$	\bigcirc	- 20	-	mA
Supply Current in			V _{DD} = 5.5 V				
NORMAL 1, 2 modes			fc=8MHz	-	12	18	
Supply Current in			fs = 32.768 kHz				mA
IDLE 1, 2 modes			$V_{IN} = 5.3 V / 0.2 V$	-	4.5	6	
Supply Current in	1		$V_{DD} = 3.0 V$				
SLOW mode	IDD		fs = 32.768 kHz	-	30	60	
Supply Current in							μA
SLEEP mode		$(C \land)$	V _{IN} = 2.8 V / 0.2 V	-	15	30	
Supply Current in			$V_{DD} = 5.5 V$				
STOP mode		$(\overline{\alpha})$	$V_{IN} = 5.3 V / 0.2 V$	-	0.5	10	μA

Note 1: Typical values show those at Topr = 25° C, $V_{DD} = 5 V$.

Note 2: Input Current I_{IN1}, I_{IN3}; The current through resistor is not included, when the input resistor (pull-up/pull-down) is contained.

			1		1	1	
Parameter	Symbol	Conditions	Min	Тур.	Max	Unit	
Analog Reference Voltage	VAREF		V _{DD} -1.5	-	V _{DD}	v	
Analog Reference Voltage	VASS	$v_{AREF} - v_{ASS} = 2.5 v$	V _{SS}	-	1.5	V V	
Analog Input Voltage	VAIN		V _{ASS}	-	VAREF	v	
Analog Supply Current	IREF	V _{AREF} = 5.5 V, V _{ASS} = 0.0 V	-	0.5	1.0	mA	
Nonlinearity Error			-	-	± 1		
Zero Point Error		$V_{AREF} - V_{ASS} \ge 2.5 V$	-	-	± 1		
Full Scale Error		,	_	_	± 1	LSE	
Total Error		$\nabla_{ASS} = 0.000 V$	_	_	± 2]	

A.C. Characterist	ics	$(V_{SS} = 0 V, V_{DD} = 4.5 \text{ to } 5.5 V, \text{ Topr} = -30 \text{ to } 70^{\circ}\text{C})$				
Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
		In NORMAL1, 2 modes	0.5	$\left(\left(\right) \right)$	10	
Marshine Coste Time		In IDLE 1, 2 modes	0.5			
Machine Cycle Time	t _{cy}	In SLOW mode	- 117.6	0-	133.3	μs
	In	In SLEEP mode				
High Level Clock Pulse Width	t _{WCH}	For external clock operation		>		
Low Level Clock Pulse Width	t _{WCL}	(XIN input), fc = 8 MHz	50	-	-	ns
High Level Clock Pulse Width	t _{WSH}	For external clock operation	1.1.7			
Low Level Clock Pulse Width	Level Clock Pulse Width t _{WSL} (XTIN input), fs = 32.768 kHz		14.7			μS
		$(7/\langle$		\bigcirc	\sim	

Recommended Oscillating Conditions ($(V_{SS} = 0 V, V_{DD} = 4.5 \text{ to } 5.5 V, \text{ Topr} =$	– 30 to 70°C)

		Oscillation		Recommended Constant		
Parameter	Oscillator	Frequency	Recommended Oscillator	C ₁	C ₂	
		8 MHz	KYOCERA KBR8.0M	2		
	Ceramic Resonator		KYOCERA KBR4.0MS	30pF	30pF	
High-frequency		4 MHz	MURATA CSA4.00MG			
Oscillation		8 MHz	TOYOCOM 210B 8.0000			
	Crystal Oscillator	4 MHz	TOYOCOM 204B 4.0000	20pF	20pF	
Low-frequency Oscillation	Crystal Oscillator	32.768 kHz	NDK MX-38T	15pF	15pF	



Note: An electrical shield by metal shied plate on the IC package should be recommend able in order to prevent the device from the high electric fieldstress applied for continuous reliable operation.



Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
Input High Voltage	V _{IH4}		V _{CC} × 0.7	(V _{cc}	v
Input Low Voltage	V _{IL4}		0	\sum	V _{CC} × 0.12	v
Power Supply Voltage	V _{cc}		5.75	6.0	6.25	v
Program Power Supply Voltage	V _{PP}		12.0	12.5	13.0	v
Initial Program Pulse Width	t _{PW}	V _{CC} = 6.0 V	0.95	1.0	1.05	ms

(2) Program Operation (High speed write mode- I) (Topr = $25 \pm 5^{\circ}$ C)



Note 1: When V_{cc} power supply is turned on or after, V_{pp} must be increased. When V_{cc} power supply is turned off or before, V_{pp} must be decreased.

Note 2: The device must not be set to the EPROM programmer or picked up from it under applying the program voltage (12.75 V \pm 0.5 V) to the V_{pp} pin as the device is damaged.

Timing Waveforms of Programming Operation

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Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
Input High Voltage	V _{IH4}		V _{CC} × 0.7	-	V _{cc}	v
Input Low Voltage	V _{IL4}		0		V _{CC} × 0.12	v
Supply Voltage	V _{CC}		6:00	6.25	6.50	v
Program Supply Voltage	V _{PP}		12.50	12.75	13.0	v
Initial Program Pulse Width	t _{PW}	V _{CC} = 6.25 V ± 0.25 V, V _{PP} = 12.75 V ± 0.25 V	0.095	0.1	0.105	ms

(3) Program Operation (High speed write mode - II) (Topr = $25 \pm 5^{\circ}$ C)



Note 1: When V_{cc} power supply is turned on or after, V_{pp} must be increased. When V_{cc} power supply is turned off or before, V_{pp} must be decreased.

Note 2: The device must not be set to the EPROM programmer or picked up from it under applying the program voltage (12.75 V \pm 0.5 V) to the V_{pp} pin as the device is damaged.



